Valery Yu Davydov

List of Publications by Year
in descending order

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192	4,148	201575	133188
papers	citations	27 h-index	59 g-index

193	193	193	4258
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Phonon dispersion and Raman scattering in hexagonal GaN and AlN. Physical Review B, 1998, 58, 12899-12907.	1.1	741
2	Raman and photoluminescence studies of biaxial strain in GaN epitaxial layers grown on 6Hâ€“SiC. Journal of Applied Physics, 1997, 82, 5097-5102.	1.1	354
3	Experimental and theoretical studies of phonons in hexagonal InN. Applied Physics Letters, 1999, 75, 3297-3299.	1.5	251
4	Composition dependence of optical phonon energies and Raman line broadening in hexagonalAlxGa1â^'xNalloys. Physical Review B, 2002, 65, .	1.1	145
5	Acceptor states in the photoluminescence spectra ofnâ^'InN. Physical Review B, 2005, 71, .	1.1	135
6	Diamond-graphite phase transition in ultradisperse-diamond clusters. Physics of the Solid State, 1997, 39, 1007-1015.	0.2	131
7	Graphene based sensor for environmental monitoring of NO2. Sensors and Actuators B: Chemical, 2016, 236, 1054-1060.	4.0	94
8	Energy gap and optical properties of InxGa1xN. Physica Status Solidi A, 2003, 195, 628-633.	1.7	92
9	Single-crystalline InN films with an absorption edge between 0.7 and 2 eV grown using different techniques and evidence of the actual band gap energy. Applied Physics Letters, 2003, 83, 4788-4790.	1.5	91
10	Phase transition-governed opalâ€“VO2 photonic crystal. Applied Physics Letters, 2001, 79, 2127-2129.	1.5	84
11	Near-infrared photoluminescence from vertical InN nanorod arrays grown on silicon: Effects of surface electron accumulation layer. Applied Physics Letters, 2006, 88, 253104.	1.5	80
12	Rehybridization of carbon on facets of detonation diamond nanocrystals and forming hydrosols of individual particles. Carbon, 2017, 122, 737-745.	5.4	72
13	Electronic and vibrational states in InN and InxGa1â^'x N solid solutions. Semiconductors, 2004, 38, 861-898.	0.2	66
14	Optically Addressable Silicon Vacancy-Related Spin Centers in Rhombic Silicon Carbide with High Breakdown Characteristics and ENDOR Evidence of Their Structure. Physical Review Letters, 2015, 115, 247602.	2.9	55
15	Physical Properties of Bulk GaN Crystals Grown by HVPE. MRS Internet Journal of Nitride Semiconductor Research, 1997, 2, 1.	1.0	53
16	Raman Spectroscopy of Lattice-Matched Graphene on Strongly Interacting Metal Surfaces. ACS Nano, 2017, 11, 6336-6345.	7.3	52
17	Insight into the performance of multi-color InGaN/GaN nanorod light emitting diodes. Scientific Reports, 2018, 8, 7311.	1.6	51
18	Strain relaxation in GaN layers grown on porous GaN sublayers. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 1.	1.0	48

#	Article	IF	Citations
19	Study of the crystal and electronic structure of graphene films grown on 6H-SiC (0001). Semiconductors, 2017, 51, 1072-1080.	0.2	44
20	MBE Growth of Hexagonal InN Films on Sapphire with Different Initial Growth Stages. Physica Status Solidi A, 1999, 176, 247-252.	1.7	41
21	Point defects in gamma-irradiated n-GaN. Semiconductor Science and Technology, 2000, 15, 73-78.	1.0	40
22	Graphene Nanoribbons for Electronic Devices. Annalen Der Physik, 2017, 529, 1700033.	0.9	39
23	InSe as a case between 3D and 2D layered crystals for excitons. Nature Communications, 2019, 10, 3479.	5.8	37
24	Correlations between electrical and optical properties for OMVPE InN. Journal of Crystal Growth, 2004, 261, 275-279.	0.7	36
25	AlGaN quantum well structures for deep-UV LEDs grown by plasma-assisted MBE using sub-monolayer digital-alloying technique. Journal of Crystal Growth, 2009, 311, 2080-2083.	0.7	36
26	Raman scattering spectra and electrical conductivity of thin silicon films with a mixed amorphous-nanocrystalline phase composition: Determination of the nanocrystalline volume fraction. Physics of the Solid State, 1997, 39, 1197-1201.	0.2	33
27	Multiwall MoS2 tubes as optical resonators. Applied Physics Letters, 2018, 113, .	1.5	30
28	Mg-Doped Hexagonal InN/Al2O3 Films Grown by MBE. Physica Status Solidi A, 1999, 176, 373-378.	1.7	29
29	Excitonic Emission in van der Waals Nanotubes of Transition Metal Dichalcogenides. Annalen Der Physik, 2019, 531, 1800415.	0.9	28
30	Fabrication and structural studies of opal-III nitride nanocomposites. Nanotechnology, 2000, 11, 291-294.	1.3	27
31	Photoluminescence and Raman study of hexagonal InN and In-rich InGaN alloys. Physica Status Solidi (B): Basic Research, 2003, 240, 425-428.	0.7	27
32	Nanoscale-crystallite nucleation and growth in amorphous solids. Physical Review B, 1995, 52, 955-966.	1.1	26
33	Unified mechanism of the surface Fermi level pinning in III-As nanowires. Nanotechnology, 2018, 29, 314003.	1.3	26
34	Creation of Negatively Charged Boron Vacancies in Hexagonal Boron Nitride Crystal by Electron Irradiation and Mechanism of Inhomogeneous Broadening of Boron Vacancy-Related Spin Resonance Lines. Nanomaterials, 2021, 11, 1373.	1.9	25
35	Characteristics of epitaxial Y-Ba-Cu-O thin films grown by aerosol MOCVD technique. Superconductor Science and Technology, 1990, 3, 493-496.	1.8	24
36	Selective excitation of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi>E</mml:mi><mml:mn>1</mml:mn></mml:msub><mml:mrow><mml:mo>(</mml:m xmlns:mml="http://www.w3.org/1998/Math/MathML"		

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37	Low-strain heteroepitaxial nanodiamonds: fabrication and photoluminescence of silicon-vacancy colour centres. Nanotechnology, 2016, 27, 395606.	1.3	23
38	Influence of Substrate Microstructure on the Transport Properties of CVD-Graphene. ACS Applied Materials & Interfaces, 2016, 8, 240-246.	4.0	23
39	Near-infrared photoluminescence of vertically aligned InN nanorods grown on Si(111) by plasma-assisted molecular-beam epitaxy. Thin Solid Films, 2006, 515, 961-966.	0.8	21
40	Towards the indium nitride laser: obtaining infrared stimulated emission from planar monocrystalline InN structures. Scientific Reports, 2018, 8, 9454.	1.6	21
41	The formation of two-layered YBa2Cu3O7- deltasuperconducting films and their microwave surface resistance. Superconductor Science and Technology, 1993, 6, 23-29.	1.8	20
42	Lattice dynamics of piezoelectric copper metaborate CuB<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>O<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>4</mml:mn></mml:msub></mml:math>. Physical Review B, 2013, 88, .	1.1	20
43	Characterization of MBEâ€grown AlGaN layers heavily doped using silane. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 315-318.	0.8	20
44	Classical and quantum solutions of the planar accumulation layer problem within the parabolic effective-mass approximation. Physical Review B, 2007, 76, .	1.1	18
45	Magnetic dynamics and spin-phonon coupling in the antiferromagnet <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Ni</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2018, 98, .	1.1	18
46	Fabrication and structure of an opal-gallium nitride nanocomposite. Semiconductor Science and Technology, 2001, 16, L5-L7.	1.0	17
47	Supersensitive graphene-based gas sensor. Technical Physics, 2016, 61, 453-457.	0.2	17
48	Molecular Beam Epitaxy of Layered Group III Metal Chalcogenides on GaAs(001) Substrates. Materials, 2020, 13, 3447.	1.3	16
49	Graphene-based biosensors. Technical Physics Letters, 2016, 42, 729-732.	0.2	15
50	Specific structural features and thermal resistance of shungite carbon to graphitization. Physics of the Solid State, 1999, 41, 1291-1294.	0.2	14
51	Lattice dynamics and a magnetic-structural phase transition in the nickel orthoborate <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi mathvariant="normal">N</mml:mi><mml:msub><mml:mi mathvariant="normal">i</mml:mi><mml:mn>3</mml:mn></mml:msub><mml:msub><mml:mrow><mml:mo>(</mml:mo><mml:mrow>	1.1	14
52	Observing visible-range photoluminescence in GaAs nanowires modified by laser irradiation. Journal of Applied Physics, 2017, 121, .	1.1	14
53	Lattice and spin dynamics in a low-symmetry antiferromagnet NiWO4. Physical Review B, 2017, 96, .	1.1	14
54	Growth of III-N/graphene heterostructures in single vapor phase epitaxial process. Journal of Crystal Growth, 2018, 504, 1-6.	0.7	14

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55	Phonons in Short-Period GaN/AlN Superlattices: Group-Theoretical Analysis, Ab initio Calculations, and Raman Spectra. Nanomaterials, 2021, 11, 286.	1.9	14
56	Monolayerâ€Thick GaN/AlN Multilayer Heterostructures for Deepâ€Ultraviolet Optoelectronics. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100242.	1.2	14
57	Anisotropic Superconductivity of InN Grown by Molecular Beam Epitaxy on Sapphire (0001). Physica Status Solidi (B): Basic Research, 2001, 228, 9-12.	0.7	13
58	III-nitride tunable cup-cavities supporting quasi whispering gallery modes from ultraviolet to infrared. Scientific Reports, 2016, 5, 17970.	1.6	13
59	Strain broadening of the 1042-nm zero phonon line of the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msup><mml:mrow><mml:mi>NV</mml:mi></mml:mrow><mml:mo>â^’</mml:mo> center in diamond: A promising spectroscopic tool for defect tomography. Physical Review B, 2017, 96, .	1.1	13
60	Experimental and theoretical studies of lattice dynamics of Mg-doped InN. Applied Physics Letters, 2007, 91, 111917.	1.5	12
61	Lattice dynamics of shortâ€period AlN/GaN superlattices: Theory and experiment. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 484-487.	0.8	12
62	Comparative characterization of graphene grown by chemical vapor deposition, transferred to nonconductive substrate, and subjected to Ar ion bombardment using X-ray photoelectron and Raman spectroscopies. Diamond and Related Materials, 2017, 76, 14-20.	1.8	12
63	Investigation of epitaxial graphene via Raman spectroscopy: Origins of phonon mode asymmetries and line width deviations. Carbon, 2020, 170, 666-676.	5.4	12
64	Lattice dynamics and Raman spectra of strained hexagonal GaN/AlN and GaN/AlGaN superlattices. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2035-2038.	0.8	11
65	Vibrational Spectra of AlNâ•GaN Superlattices: Theory and Experiment. Physics of the Solid State, 2005, 47, 742.	0.2	11
66	Investigation of Statistical Broadening in InGaN Alloys. Journal of Physics: Conference Series, 2018, 1135, 012050.	0.3	11
67	Intercalation of Iron Atoms under Graphene Formed on Silicon Carbide. Physics of the Solid State, 2018, 60, 1439-1446.	0.2	11
68	Properties of AlN single crystals doped with Beryllium via high temperature diffusion. Applied Physics Letters, 2018, 113, .	1.5	11
69	Crystal Structure, Raman Spectroscopy and Dielectric Properties of New Semiorganic Crystals Based on 2-Methylbenzimidazole. Crystals, 2019, 9, 573.	1.0	11
70	Lattice dynamics and electronic structure of cobaltâ€“titanium spinel Co2TiO4. Physics of the Solid State, 2016, 58, 2516-2522.	0.2	10
71	Local Anodic Oxidation of Graphene Layers on SiC. Technical Physics Letters, 2018, 44, 381-383.	0.2	10
72	Cobalt Intercalation of Graphene on Silicon Carbide. Physics of the Solid State, 2019, 61, 1316-1326.	0.2	10

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73	MoSe₂/graphene/6H-SiC heterojunctions: energy band diagram and photodegradation. Semiconductor Science and Technology, 2019, 34, 125007.	1.0	10
74	Localization and transient emission properties in InGaN/GaN quantum wells of different polarities within coreâ€“shell nanorods. Nanoscale, 2019, 11, 193-199.	2.8	10
75	Radiation Defects in Heterostructures 3C-SiC/4H-SiC. Crystals, 2019, 9, 115.	1.0	10
76	State-of-the-art and prospects for intense red radiation from coreâ€“shell InGaN/GaN nanorods. Scientific Reports, 2020, 10, 19048.	1.6	10
77	The influence of growth temperature on the structural characteristics of YBa2Cu3O7- deltafilms: a Raman scattering study. Superconductor Science and Technology, 1993, 6, 819-821.	1.8	9
78	AlGaN epitaxial layers grown by HVPE on sapphire substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1483-1486.	0.8	9
79	High Quality Graphene Grown by Sublimation on 4H-SiC (0001). Semiconductors, 2018, 52, 1882-1885.	0.2	9
80	Optical Estimation of the Carrier Concentration and the Value of Strain in Monolayer Graphene Grown on 4H-SiC. Semiconductors, 2019, 53, 1904-1909.	0.2	9
81	Formation and Raman spectroscopic study of YBCO/STO/YBCO heteroepitaxial structures. Superconductor Science and Technology, 1994, 7, 727-733.	1.8	8
82	Statistical Ga clusters andA1(TO)gap mode inAlxGa1â^'xNalloys. Physical Review B, 2000, 62, 2522-2535.	1.1	8
83	Study of the correlation between GaN material properties and the growth conditions of radio frequency plasma-assisted molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 304-308.	1.7	8
84	Stress-induced changes of thermal donor formation in heat-treated Czochralski-grown silicon. Physica B: Condensed Matter, 2003, 340-342, 769-772.	1.3	8
85	Deformation of AlGaN/GaN superlattice layers according to x-ray diffraction data. Physics of the Solid State, 2004, 46, 364-370.	0.2	8
86	GaN Films Grown by Vapor-Phase Epitaxy in a Hydrideâ€“Chloride System on Si(111) Substrates with AlN Buffer Sublayers. Technical Physics Letters, 2005, 31, 915.	0.2	8
87	EXAFS study of GaN/AlN multiple quantum wells grown by ammonia MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 311-314.	0.8	8
88	Structure and composition of silicon microarrays subjected to cyclic insertion and extraction of lithium. Technical Physics, 2015, 60, 531-540.	0.2	8
89	Gallium nitride nanowires and microwires with exceptional length grown by metal organic chemical vapor deposition via titanium film. Journal of Applied Physics, 2015, 117, 024301.	1.1	8
90	Effect of the Sapphire-Nitridation Level and Nucleation-Layer Enrichment with Aluminum on the Structural Properties of AlN Layers. Semiconductors, 2018, 52, 789-796.	0.2	8

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91	Molecular-Beam Epitaxy of Two-Dimensional GaSe Layers on GaAs(001) and GaAs(112) Substrates: Structural and Optical Properties. Semiconductors, 2019, 53, 1131-1137.	0.2	8
92	Lattice and magnetic dynamics in the polar, chiral, and incommensurate antiferromagnet <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">Ni</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="normal">InSbO</mml:mi><mml:mn>6</mml:mn></mml:msub></mml:math>. Physical Review B, 2019, 100, .	1.1	8
93	Quasi-freestanding graphene on SiC(0001) via cobalt intercalation of zero-layer graphene. Physical Review B, 2021, 104, .	1.1	8
94	Manifestation of the equilibrium hole distribution in photoluminescence of n-InN. Physica Status Solidi (B): Basic Research, 2005, 242, R33-R35.	0.7	7
95	Band bending of n-InN epilayers and exact solution of the classical Thomasâ€“Fermi equation. Physica Status Solidi - Rapid Research Letters, 2007, 1, 159-161.	1.2	7
96	SIMS and Raman studies of Mgâ€doped InN. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1648-1651.	0.8	7
97	New photoelectrical properties of InN: Interband spectra and fast kinetics of positive and negative photoconductivity of InN. Journal of Applied Physics, 2018, 123, .	1.1	7
98	A Computational and Spectroscopic Study of the Electronic Structure of V2O5-Based Cathode Materials. Journal of Physical Chemistry C, 2021, 125, 5848-5858.	1.5	7
99	Neutron transmutation doping of silicon 30Si monoisotope with phosphorus. Technical Physics Letters, 2006, 32, 550-553.	0.2	6
100	Radiation-produced defects in n-GaN. Physica B: Condensed Matter, 2007, 401-402, 315-318.	1.3	6
101	Selective area growth of N-polar GaN nanorods by plasma-assisted MBE on micro-cone-patterned c-sapphire substrates. Journal of Crystal Growth, 2017, 477, 207-211.	0.7	6
102	Study of properties and development of sensors based on graphene films grown on SiC (0001) by thermal destruction method. Journal of Physics: Conference Series, 2018, 951, 012007.	0.3	6
103	Optical and electrical properties of the MoSe₂/graphene heterostructures. Journal of Physics: Conference Series, 2018, 1092, 012002.	0.3	6
104	Lattice dynamics and electronic transitions in a structurally complex layered copper borate <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Cu</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2017, 96, .	1.1	6
105	Shallow donor centers in gallium nitrides. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 601-604.	0.8	5
106	InN-based layers grown by modified HVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1444-1447.	0.8	5
107	Photoluminescence of n-InN with low electron concentrations. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 50-58.	0.8	5
108	Specific features of Raman spectra of IIIâ€“V nanowhiskers. Physics of the Solid State, 2011, 53, 1431-1439.	0.2	5

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109	X-ray diffraction study of short-period AlN/GaN superlattices. Crystallography Reports, 2013, 58, 953-958.	0.1	5
110	Synthesis of GaN nano- and microwire crystals induced by a titanium nanolayer. Technical Physics Letters, 2014, 40, 372-374.	0.2	5
111	IIIâ€nitride microcrystal cavities with quasi whispering gallery modes grown by molecular beam epitaxy. Physica Status Solidi (B): Basic Research, 2016, 253, 845-852.	0.7	5
112	Lattice and magnetic dynamics of a quasi-one-dimensional chain antiferromagnet PbFeBO4. Journal of Physics Condensed Matter, 2017, 29, 025808.	0.7	5
113	Intercalation Synthesis of Cobalt Silicides under Graphene Grown on Silicon Carbide. Physics of the Solid State, 2020, 62, 519-528.	0.2	5
114	The Effect of Interface Diffusion on Raman Spectra of Wurtzite Short-Period GaN/AlN Superlattices. Nanomaterials, 2021, 11, 2396.	1.9	5
115	On fermi resonance theory. Physica Status Solidi (B): Basic Research, 1976, 78, 359-370.	0.7	4
116	Lattice dynamics of ferroelectric NaNO2by two-phonon Raman scattering and infrared absorption. Ferroelectrics, 1978, 21, 337-338.	0.3	4
117	Influence of rapid high-temperature anneals on the photoluminescence of erbium-doped GaN in the wavelength interval 1.0â€“1.6 Âµm. Semiconductors, 1999, 33, 1-5.	0.2	4
118	Preparation and properties of isotopically pure polycrystalline silicon. Semiconductors, 2001, 35, 877-879.	0.2	4
119	Bulk gallium nitride: preparation and study of properties. Physica Status Solidi A, 2003, 195, 122-126.	1.7	4
120	Optical phonons in hexagonal GaN/AlN and GaN/AlGaN superlattices. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2389-2393.	0.8	4
121	Resonant raman scattering and dispersion of polar optical and acoustic phonons in hexagonal inn. Semiconductors, 2010, 44, 161-170.	0.2	4
122	Electron-beam modification of the parameters of the insulator-metal phase transition in vanadium dioxide films. Technical Physics Letters, 2013, 39, 705-708.	0.2	4
123	Defects and stresses in MBE-grown GaN and Al0.3Ga0.7N layers doped by silicon using silane. Crystallography Reports, 2013, 58, 1023-1029.	0.1	4
124	Photoluminescence Spectra of thin Zno films grown by ALD technology. Physics of the Solid State, 2015, 57, 1865-1869.	0.2	4
125	Elastic strains and delocalized optical phonons in AlN/GaN superlattices. Semiconductors, 2016, 50, 1043-1048.	0.2	4
126	On the laser detachment of n-GaN films from substrates, based on the strong absorption of IR light by free charge carriers in n +-GaN substrates. Semiconductors, 2016, 50, 699-704.	0.2	4

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127	State memory in solution gated epitaxial graphene. Applied Surface Science, 2018, 444, 36-41.	3.1	4
128	Photoluminescence Kinetics of Dark and Bright Excitons in Atomically Thin MoS₂. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100263.	1.2	4
129	Comparative low-frequency noise studies of YBaCuO films. AIP Conference Proceedings, 1993, , .	0.3	3
130	Investigation of vacancy-type complexes in GaN and AlN using positron annihilation. Semiconductors, 2002, 36, 1106-1110.	0.2	3
131	Iron disilicide formed in a-Siã€ˆFeã€‰ thin films by magnetron co-sputtering. Physica B: Condensed Matter, 2003, 340-342, 939-943.	1.3	3
132	Resonant Raman scattering in InGaN alloys. Physica Status Solidi (B): Basic Research, 2006, 243, 1494-1498.	0.7	3
133	Various types of GaN/InGaN nanostructures grown by MOCVD on Si(111) substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 441-444.	0.8	3
134	Chemical modification of InN surface with sulfide solution. Applied Surface Science, 2017, 422, 1052-1058.	3.1	3
135	Excitonic lasing of strain-free InP(As) quantum dots in AlInAs microdisk. Applied Physics Letters, 2017, 110, .	1.5	3
136	Site-controlled GaN nanocolumns with InGaN insertions grown by MBE. Journal of Physics: Conference Series, 2017, 917, 032032.	0.3	3
137	Transport properties of graphene films grown by thermodestruction of SiC (0001) surface in argon medium. Technical Physics Letters, 2017, 43, 849-852.	0.2	3
138	Phonons in short-period (GaN)_m(AlN)_n superlattices: ab initio calculations and group-theoretical analysis of modes and their genesis. Journal of Physics: Conference Series, 2019, 1400, 066016.	0.3	3
139	Modification of the Electronic Structure of Quasi-Free-Standing Graphene by the Adsorption and Intercalation of Mn Atoms. Journal of Experimental and Theoretical Physics, 2021, 132, 906-916.	0.2	3
140	Graphene on silicon carbide as a basis for gas- and biosensor applications. Nanosystems: Physics, Chemistry, Mathematics, 2018, , 95-97.	0.2	3
141	Croconic Acid Doped Triglycine Sulfate: Crystal Structure, UV-Vis, FTIR, Raman, Photoluminescence Spectroscopy, and Dielectric Properties. Crystals, 2022, 12, 679.	1.0	3
142	Crystalline structure of a C60/C70 membrane. Physics of the Solid State, 1998, 40, 535-538.	0.2	2
143	Electronic and structural properties of InN thin films grown by MOMBE on sapphire substrates. , 2000, , .		2
144	<title>Bandgap of hexagonal InN and InGaN alloys</title>. , 2002, , .		2

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145	The formation of Î²-FeSi2 precipitates in microcrystalline Si. Semiconductors, 2002, 36, 1235-1239.	0.2	2
146	Isotope-pure silicon layers grown by MBE. Semiconductors, 2002, 36, 1400-1402.	0.2	2
147	Resonant Raman scattering spectra in a ZnCdSe/ZnSe structure with a quantum well and open nanowires. Physics of the Solid State, 2003, 45, 1374-1378.	0.2	2
148	Fullerene films highly resistant to laser radiation. Technical Physics, 2004, 49, 258-262.	0.2	2
149	Compositional fluctuations in isotopic solid solutions. Physics of the Solid State, 2007, 49, 46-54.	0.2	2
150	MOVPE-grown n-In_xGa_{1-x}N (x~0.5)/p-Si(111) template as a novel substrate. Proceedings of SPIE, 2013, , .	0.8	2
151	Mode adjustment in hexagonal microresonators with an active region. Journal of Physics: Conference Series, 2016, 741, 012126.	0.3	2
152	Resonance energy transfer in a dense array of IIâ€“VI quantum dots. Physics of the Solid State, 2016, 58, 2256-2260.	0.2	2
153	Optical and Structural Properties of Composite Si:Au Layers Formed by Laser Electrodispersion. Semiconductors, 2016, 50, 418-425.	0.2	2
154	Transport properties of graphene in the region of its interface with water surface. Physics of the Solid State, 2016, 58, 1483-1486.	0.2	2
155	On the laser lift-off of lightly doped micrometer-thick n-GaN films from substrates via the absorption of IR radiation in sapphire. Semiconductors, 2017, 51, 115-121.	0.2	2
156	Template Synthesis of Monodisperse Submicrometer Spherical Nanoporous Silicon Particles. Semiconductors, 2019, 53, 1048-1053.	0.2	2
157	Emission Properties of Heavily Doped Epitaxial Indium-Nitride Layers. Semiconductors, 2019, 53, 1357-1362.	0.2	2
158	Detection of lysine molecular ions in solution gated field effect transistors based on unmodified graphene. Journal of Applied Physics, 2020, 128, 215302.	1.1	2
159	Mechanical scanning probe lithography of nanophotonic devices based on multilayer TMDCs. Journal of Physics: Conference Series, 2021, 2015, 012020.	0.3	2
160	The â€œdestructiveâ€•fermi resonance. Physica Status Solidi (B): Basic Research, 1977, 79, 347-357.	0.7	1
161	Anomalies in the microwave conductivity of a polycrystalline C60 membrane. Physics of the Solid State, 1998, 40, 532-534.	0.2	1
162	Isotope-pure 28Si layers grown by VPE. Semiconductors, 2002, 36, 1398-1399.	0.2	1

#	Article	IF	Citations
163	Bulk large-area GaN layers. Technical Physics Letters, 2003, 29, 400-403.	0.2	1
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